

INTERCONNECTS USING METAL SPACERS AND METHOD
FOR FORMING SAME

ABSTRACT

The preferred embodiment of the present invention provides increased conductivity between interlevel interconnection lines. The preferred embodiment uses sidewall spacers (120, 122) on the sides of the interconnection lines (104, 106) to increase the contact area between interconnection lines (104, 106) and interconnect studs (102). This increase in area improves connection resistance and allows further device scaling without unacceptable decreases in the conductivity of the connection, and without adding significant expense in the fabrication process.

Fig. 1